

HB0680

Silicon epitaxial planar type

For waveform clipper and surge absorption circuit

Bi-directional type

■ Features

- Eco-friendly Halogen-free package

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	I_{FRM}	200	mA
Total power dissipation *1	P_T	150	mW
Electrostatic discharge *2	ESD	± 15	kV
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

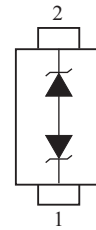
Note) *1: $P_T = 150$ mW achieved with a printed circuit board.

*2: Test method: IEC61000-4-2 (C = 150 pF, R = 330 Ω , Contact discharge: 10 times)

■ Package

- Code
SSMini2-F5-B
- Pin Name
1. Cathode
2. Cathode

■ Marking Symbol: GH



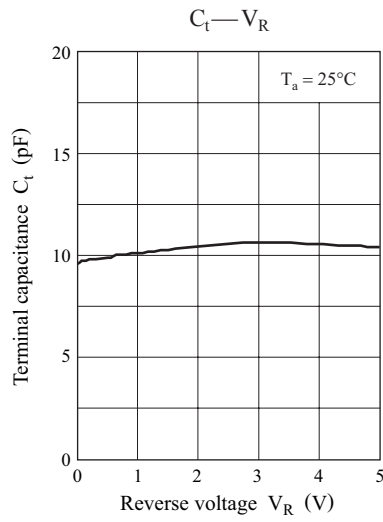
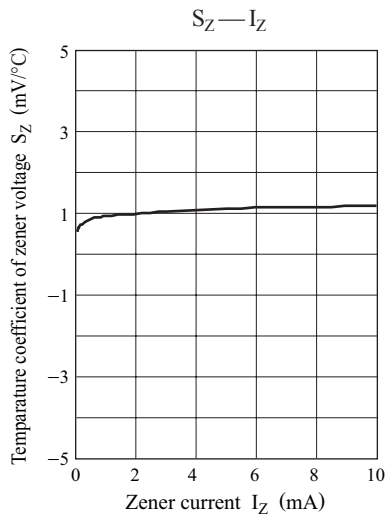
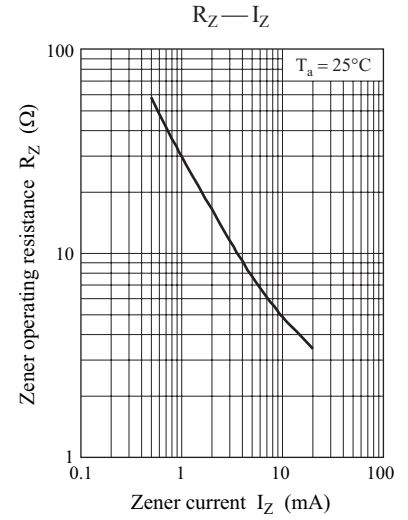
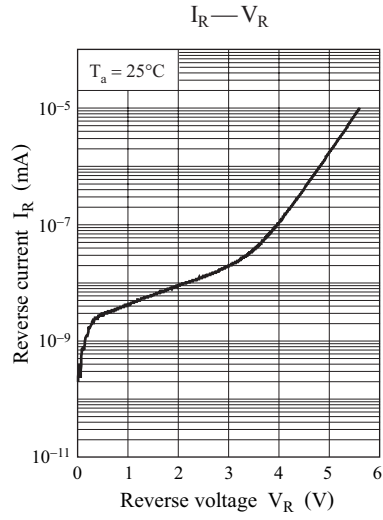
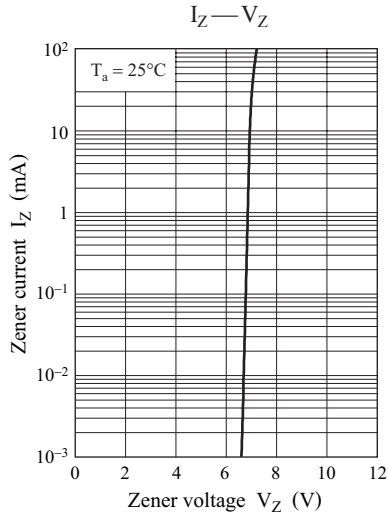
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Zener voltage *1,2	V_Z	$I_Z = 5$ mA	6.50		7.50	V
Zener operating resistance	R_Z	$I_Z = 5$ mA			20	Ω
Reverse current	I_R	$V_R = 4.0$ V			50	nA
Terminal capacitance	C_t	$V_R = 0$ A, $f = 1$ MHz		15.0		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. *1: The temperature must be controlled 25°C for V_Z measurement. V_Z value measured at other temperature must be adjusted to $V_Z (25^\circ\text{C})$

*2: V_Z guaranteed 20 ms after current flow.



SSMini2-F5-B

Unit: mm

